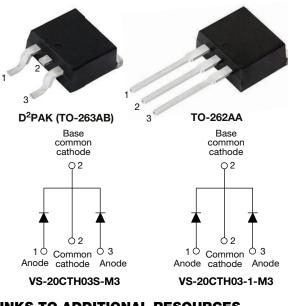
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SHAY

VS-20CTH03S-M3, VS-20CTH03-1-M3

Vishay Semiconductors

Hyperfast Rectifier, 2 x 10 A FRED Pt[®]



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACT	ERISTICS
I _{F(AV)}	2 x 10 A
V _R	300 V
V _F at I _F	0.85 V
t _{rr} max.	35 ns
T _J max.	175 °C
Package	D ² PAK (TO-263AB), TO-262AA
Circuit configuration	Common cathode

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Meets JESD 201, class 1A whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Vishay Semiconductors 300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

MECHANICAL DATA

Case: D²PAK (TO-263AB), TO-262AA

Molding compound meets UL 94 V-0 flammability rating **Terminal:** matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM R	ATINGS				
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS
Peak repetitive reverse voltage		V _{RRM}		300	V
Average rectified forward current	per diode		T _C = 160 °C	10	
Average rectilied forward current	per device	IF(AV)		20	А
Non-repetitive peak surge current		I _{FSM}	T _J = 25 °C	120	
Operating junction and storage tem	peratures	T _J , T _{Stg}		-65 to +175	°C

ELECTRICAL SPECIFICAT	IONS (T _J	= 25 °C unless otherwise specified)				
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	300	-	-	
Forward voltage	VF	I _F = 10 A	-	1.05	1.25	V
Forward voltage	۷F	I _F = 10 A, T _J = 125 °C	-	0.85	0.95	
Reverse leakage current	1_	$V_{R} = V_{R}$ rated	-	-	20	uА
neverse leakage current	IR	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	6	200	μΑ
Junction capacitance	CT	V _R = 300 V	-	30	-	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH

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HALOGEN

FREE



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DYNAMIC RECOVERY CHARA	CTERIST	ICS (T _C = 25 °C ι	unless otherwise s	specified	d)		
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	50 A/µs, V _R = 30 V	-	-	35	
Reverse recovery time	+	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	$I_F = 1.0 \text{ A}, \text{ d}_F/\text{d}t = 100 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	30	
	t _{rr}	T _J = 25 °C	$I_{\rm F} = 10 {\rm A}$	-	31	-	ns
		T _J = 125 °C		-	42	-	
Poole recovery ourrent	I	T _J = 25 °C		-	2.4	-	
Peak recovery current	I _{RRM}	T _J = 125 °C	dl _F /dt = 200 A/µs V _B = 200 V	-	5.6	-	A
Reverse recovery charge	Q _{rr}	T _J = 25 °C	- 36 -	nC			
neverse recovery charge	Qrr	T _J = 125 °C		-	120	-	no

THERMAL - MECHANICAL S	PECIFICAT	TIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to case per diode	R _{thJC}		-	-	1.5	°C/W
Thermal resistance, junction to ambient	R _{thJA}		-	-	70	°C/W
Weight			-	2.0	-	g
weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style D ² PAK (TO-263AB)	20CTH03S			
		Case style TO-262AA		20CT	H03-1	

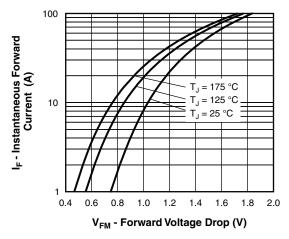


Fig. 1 - Maximum Forward Voltage Drop Characteristics

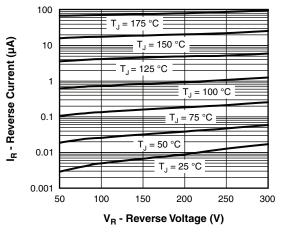


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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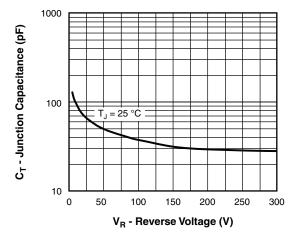


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

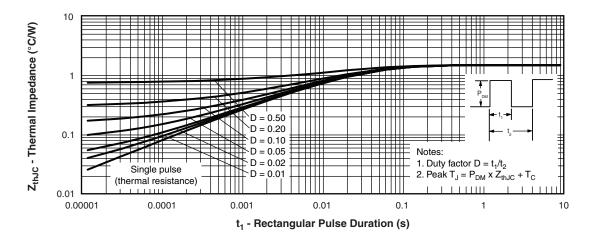
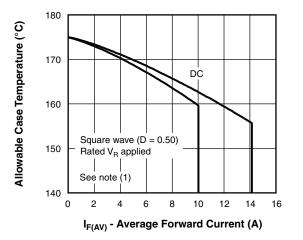
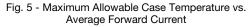


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

Average Power Loss (W)





Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \, \mathsf{x} \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \, \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \\ \end{array}$

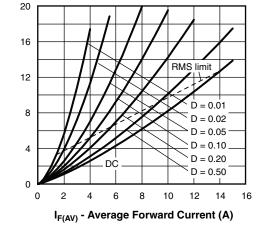


Fig. 6 - Forward Power Loss Characteristics

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VS-20CTH03S-M3, VS-20CTH03-1-M3

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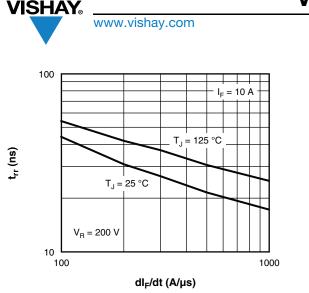


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

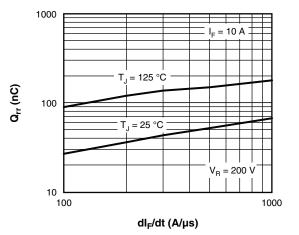
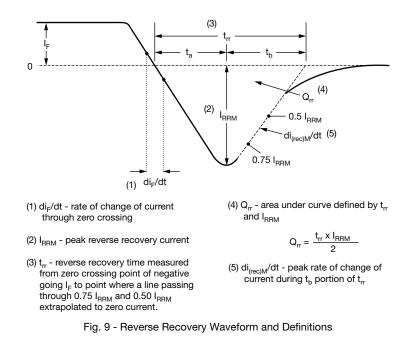
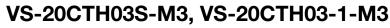


Fig. 8 - Typical Stored Charge vs. dl_F/dt

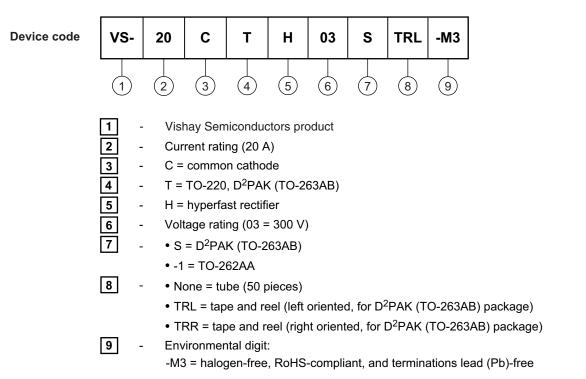




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ORDERING INFORMATION TABLE

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ORDERING INFORMATION (Example)					
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION			
VS-20CTH03S-M3	50	Antistatic plastic tubes			
VS-20CTH03STRL-M3	800	13" diameter plastic tape and reel			
VS-20CTH03STRR-M3	800	13" diameter plastic tape and reel			
VS-20CTH03-1-M3	50	Antistatic plastic tubes			

	LINKS TO RELATE	D DOCUMENTS
Dimensions	D ² PAK (TO-263AB)	www.vishay.com/doc?96164
Dimensions	TO-262AA	www.vishay.com/doc?96165
Part marking information	D ² PAK (TO-263AB)	www.vishay.com/doc?95444
Part marking information	TO-262AA	www.vishay.com/doc?95443
Packaging information	D ² PAK (TO-263AB)	www.vishay.com/doc?96424
SPICE model		www.vishay.com/doc?96583

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D²PAK

DIMENSIONS in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
A	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STNDUL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25	BSC	0.010	BSC	
L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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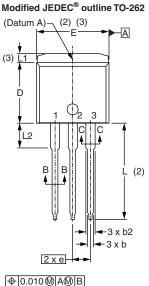
Outline Dimensions

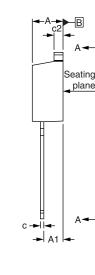


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TO-262AA

DIMENSIONS in millimeters and inches





F D1 (3) (3) Section A - A Base (4) Plating b1. b3 metal ≰ c1 (4) -(b, b2)-Section B - B and C - C Scale: None





Diodes 1. - Anode (two die)/open (one die) 2., 4. - Cathode 3. - Anode

Lead assignments

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	BSC	0.100) BSC	
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

 ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the second dimensioner of the second dimensis of the second dimensioner of the second dimensioner of the the outmost extremes of the plastic body (3)

Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only (5)

Controlling dimension: inches

(6) Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)

Revision: 30-Nov-17

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